

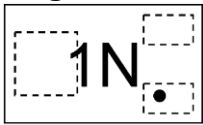


GP3904Y3 Transistor(NPN)

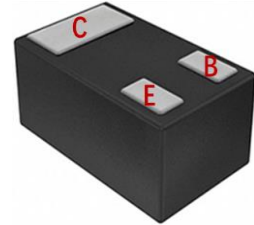
Feature

- Switching Transistor
- Collector-emitter voltage $V_{CE}=40V$
- Collector current $I_c=0.2A$

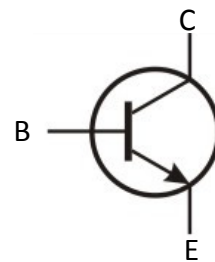
Marking: 1N



DFN1006-3L



Schematic diagram



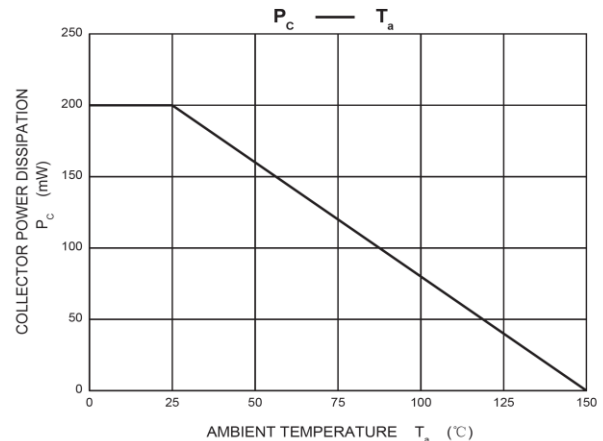
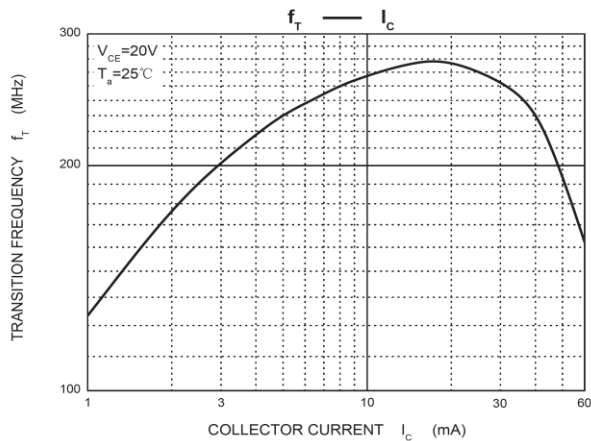
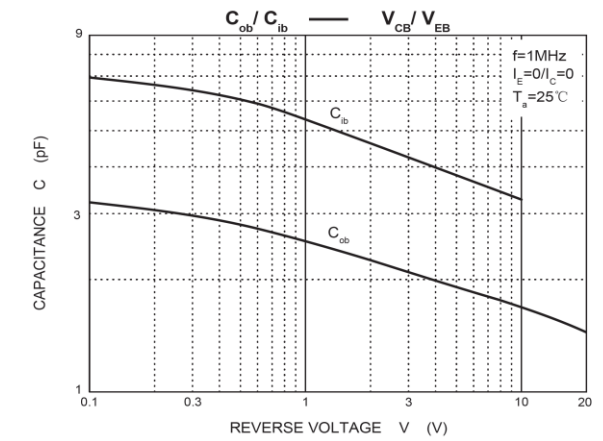
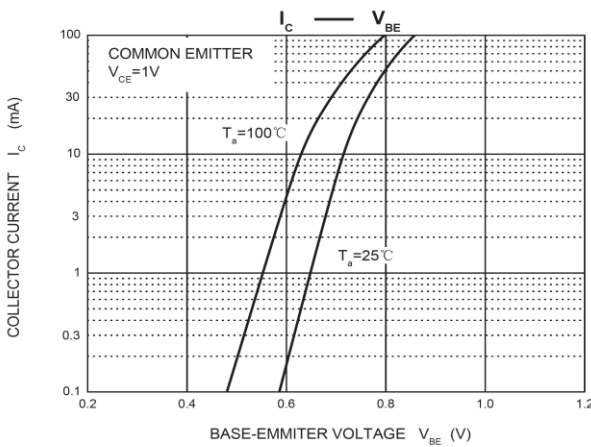
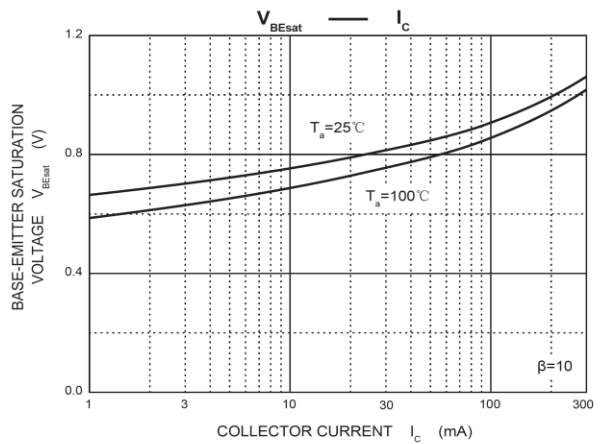
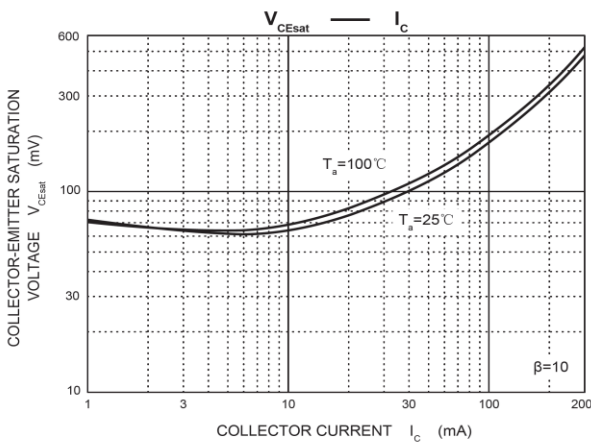
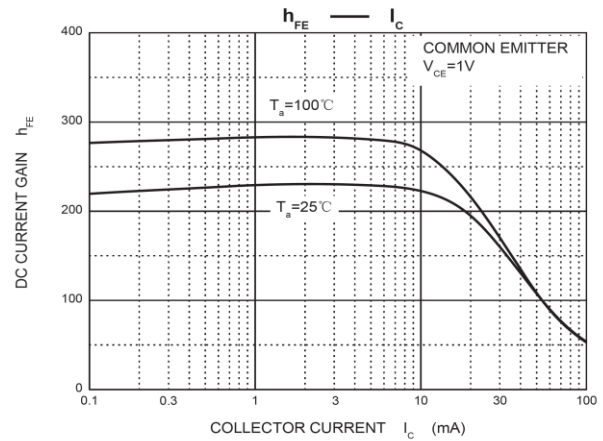
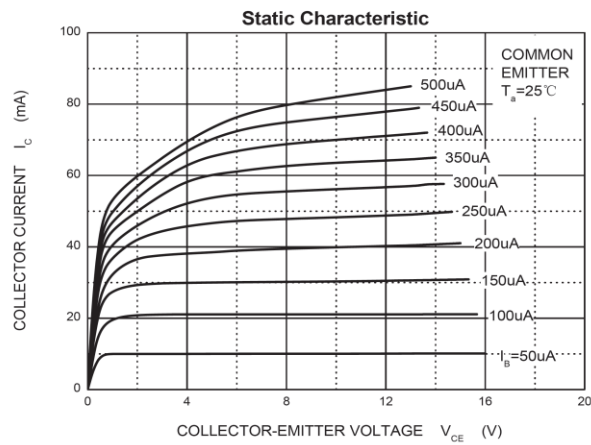
MAXIMUM RATINGS ($T_a=25^{\circ}C$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	60	V
Collector-Emitter Voltage	V_{CEO}	40	V
Emitter-Base Voltage	V_{EBO}	6	V
Collector Current -Continuous	I_c	0.2	A
Power Dissipation	P_d	0.1	W
Junction Temperature	T_J	150	$^{\circ}C$
Storage Temperature	T_{STG}	-55~ +150	$^{\circ}C$

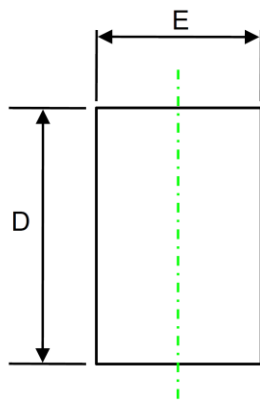
ELECTRICAL CHARACTERISTICS($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=10\mu\text{A}, I_E=0$	60		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1\text{mA}, I_B=0$	40		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=10\mu\text{A}, I_C=0$	6		V
Collector cut-off current	I_{CBO}	$V_{CB}=60\text{V}, I_E=0$		100	nA
Collector cut-off current	I_{CEX}	$V_{CE}=30\text{V}, V_{EB(off)}=3\text{V}$		50	nA
Base cut-off current	I_{BEX}			50	nA
Emitter cut-off current	I_{EBO}	$V_{EB}=5\text{V}, I_C=0$		100	nA
DC current gain	h_{FE1}	$V_{CE}=1\text{V}, I_C=0.1\text{mA}$	40		
	h_{FE2}	$V_{CE}=1\text{V}, I_C=1\text{mA}$	70		
	h_{FE3}	$V_{CE}=1\text{V}, I_C=10\text{mA}$	100	300	
	h_{FE4}	$V_{CE}=1\text{V}, I_C=50\text{mA}$	60		
	h_{FE5}	$V_{CE}=1\text{V}, I_C=100\text{mA}$	30		
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=50\text{mA}, I_B=0\text{mA}$		0.3	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=50\text{mA}, I_B=0\text{mA}$		0.95	V
Transition frequency	f_T	$V_{CE}=20\text{V}, I_C=10\text{mA}, f=100\text{MHz}$	300		MHZ
Delay Time	t_d	$V_{CC}=3\text{V}, I_C=10\text{mA}, V_{BE(off)}=-0.5\text{V}, I_{B1}=1\text{mA}$		35	ns
Rise Time	t_r			35	ns
Storage Time	t_s	$V_{CC}=3\text{V}, I_C=10\text{mA}, I_{B1}=I_{B2}=1\text{mA}$		200	ns
Fall Time	t_f			50	ns

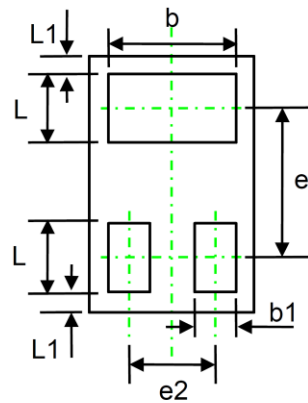
Typical Characteristics



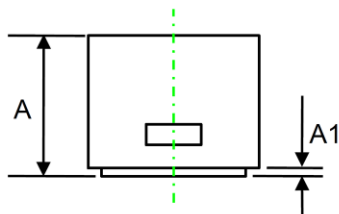
DFN1006-3L Package Information



TOP VIEW
[顶视图]



BOTTOM VIEW
[底视图]



SIDE VIEW
[侧视图]

	Dimensions In Millimeters		
	Min.	Typ.	Max.
A	0.43	0.45	0.47
D	0.95	1.00	1.05
E	0.55	0.60	0.65
b	0.45	0.50	0.55
e	-	0.65	-
e2	-	0.35	-
L	0.20	0.25	0.30
L1	0.05 REF.		
b1	0.10	0.15	0.20

单击下面可查看定价，库存，交付和生命周期等信息

[>>GP\(格瑞宝\)](#)